

● FEATURES:

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_F$ : 30 mA

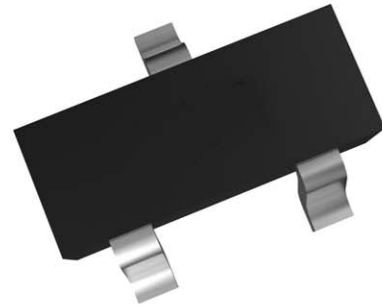
Collector-base voltage

$V_R$ : 40 V

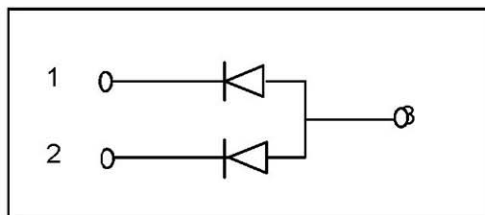
Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$

SOT-323



CIRCUIT:



MARKING: 3E

● ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	$I_R$	$V_R=10\text{V}$		1	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=1\text{mA}$		0.37	V
Diode capacitance	$C_D$	$V_R=1\text{V}, f=1\text{MHz}$		5	pF